

N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY

V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)
30	0.028 at V _{GS} = 10 V	8 ^a	6.2
	0.038 at V _{GS} = 4.5 V	7	

FEATURES

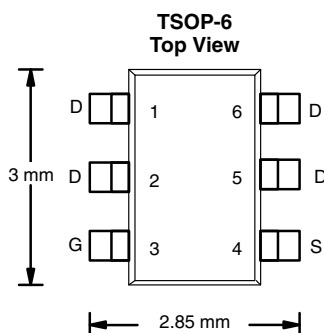
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Material categorization:
For definitions of compliance please see
www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Load Switch for Portable Devices

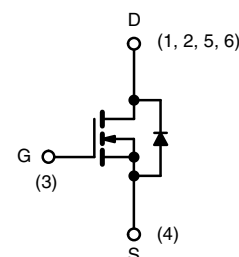


Marking Code

AG XX

Lot Traceability
and Date Code

Part # Code



N-Channel MOSFET

Ordering Information: Si3424BDV-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _C = 25 °C	A
		T _C = 70 °C	
		T _A = 25 °C	
		T _A = 70 °C	
Pulsed Drain Current	I _{DM}	30	
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	A
		T _A = 25 °C	
Maximum Power Dissipation ^a	P _D	T _C = 25 °C	W
		T _C = 70 °C	
		T _A = 25 °C	
		T _A = 70 °C	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^c	R _{thJA}	50	60	°C/W
		90	110	
Maximum Junction-to-Foot (Drain)	R _{thJF}	35	42	

Notes:

- Package limited.
- Based on T_C = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.

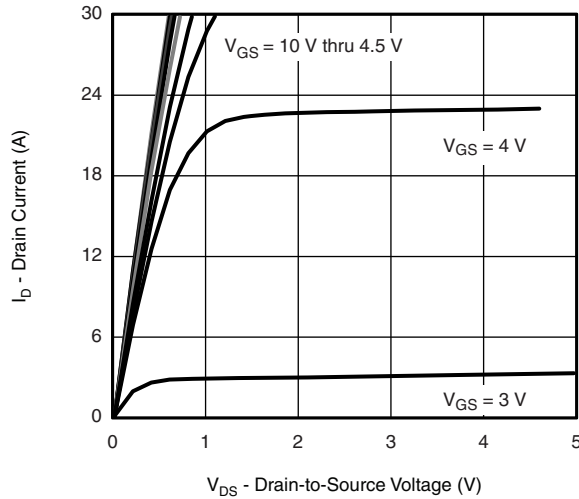
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	30			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		23.75		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			5.8		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1		3	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	μA
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 85 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = ≥ 5 V, V _{GS} = 10 V	30			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 7 A		0.0230	0.0280	Ω
		V _{GS} = 4.5 V, I _D = 5.8 A		0.0315	0.0380	
Forward Transconductance	g _{fs}	V _{DS} = 15 V, I _D = 7 A		17		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		735		pF
Output Capacitance	C _{oss}			130		
Reverse Transfer Capacitance	C _{rss}			34		
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 7 A		13.05	19.6	nC
		V _{DS} = 24 V, V _{GS} = 4.5 V, I _D = 7 A		6.2	9.3	
Q _{gs}			2.16			
Q _{gd}			2.15			
Gate Resistance	R _g	f = 1 MHz		2.45	3.7	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 2.7 Ω I _D ≅ 5.6 A, V _{GEN} = 10 V, R _g = 1 Ω		4.5	6.8	ns
Rise Time	t _r			10	15	
Turn-Off DelayTime	t _{d(off)}			16	24	
Fall Time	t _f			7	10.5	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 3.2 Ω I _D ≅ 4.7 A, V _{GEN} = 4.5 V, R _g = 1 Ω		18	27	
Rise Time	t _r			85	128	
Turn-Off DelayTime	t _{d(off)}			17	26	
Fall Time	t _f			12	18	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			2.48	A
Pulse Diode Forward Current ^a	I _{SM}				30	
Body Diode Voltage	V _{SD}	I _S = 3 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 3.2 A, dI/dt = 100 A/μs		13.8	20.7	nC
Body Diode Reverse Recovery Charge	Q _{rr}			6.21	9.32	ns
Reverse Recovery Fall Time	t _a			8.5		
Reverse Recovery Rise Time	t _b			5.3		

Notes:

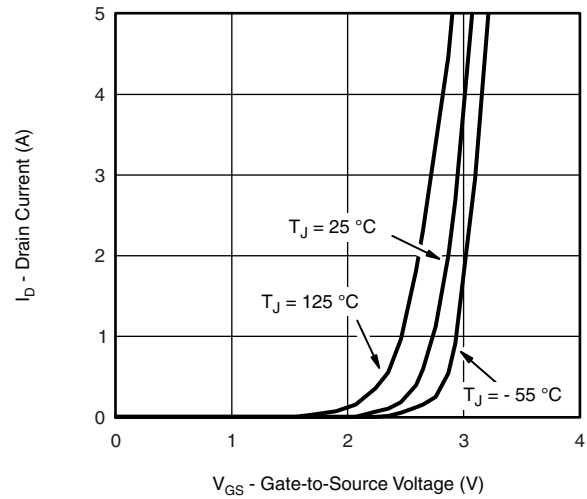
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

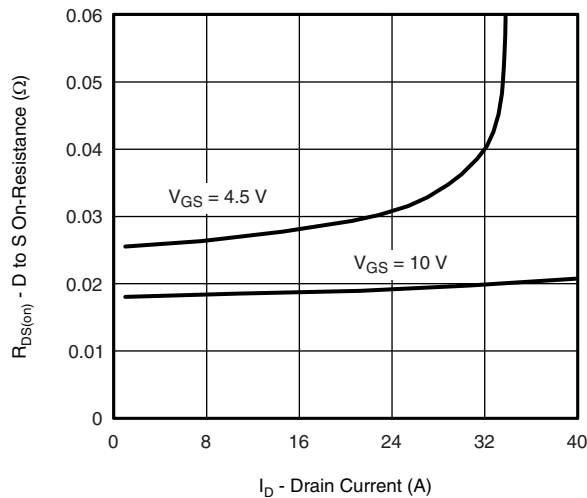
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



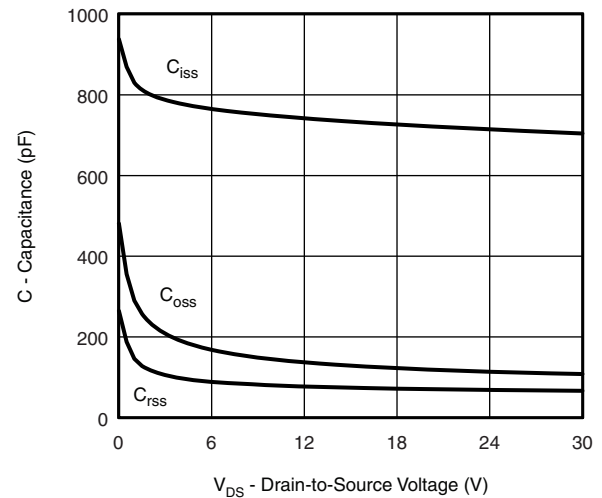
Output Characteristics



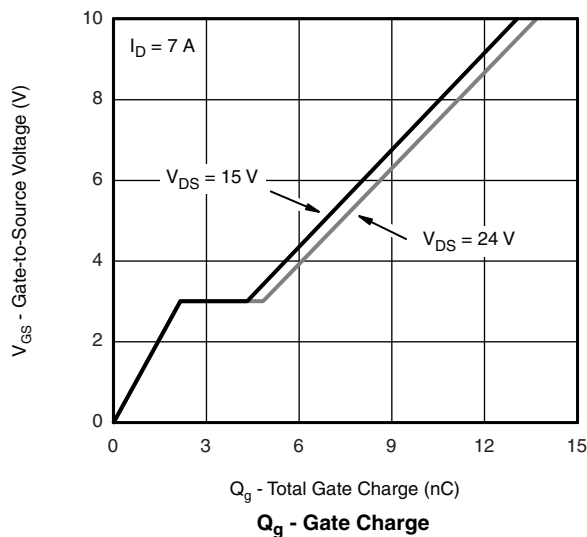
Transfer Characteristics curves vs. Temp



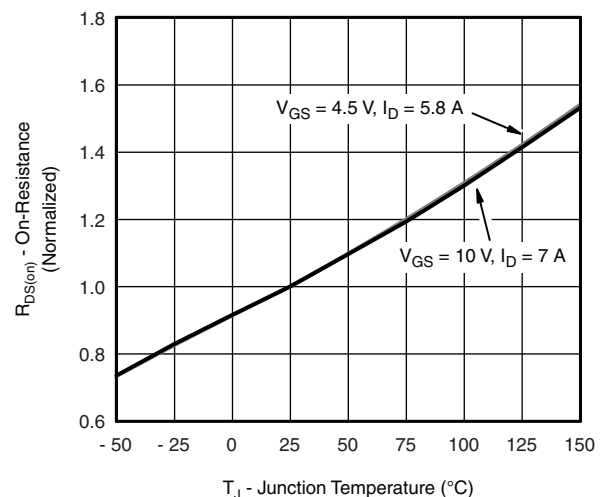
On-Resistance vs. Drain Current



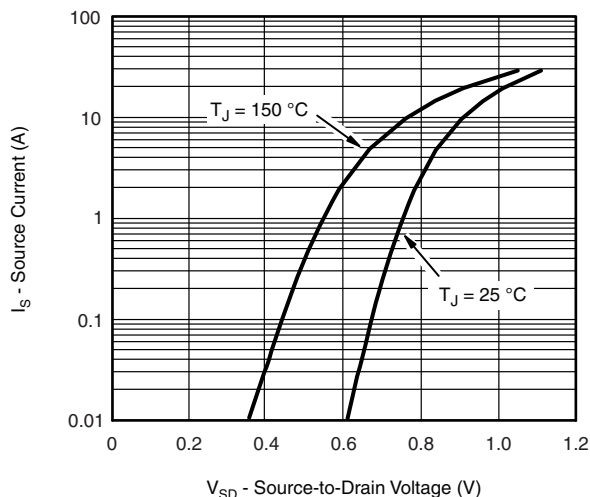
Capacitance



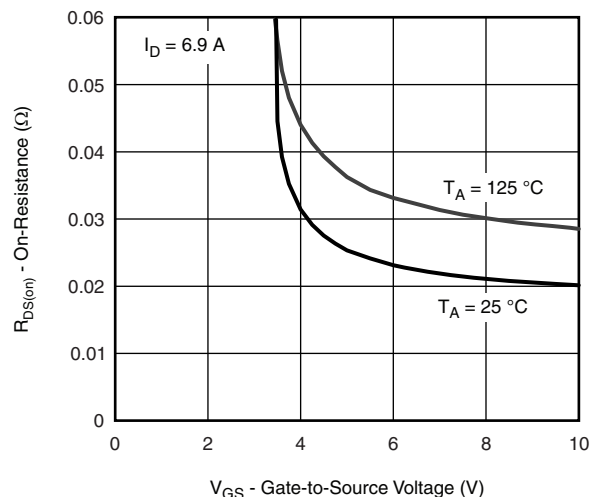
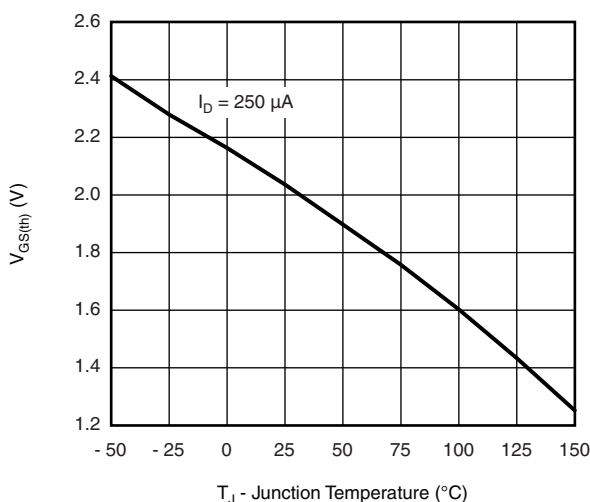
Q_g - Gate Charge



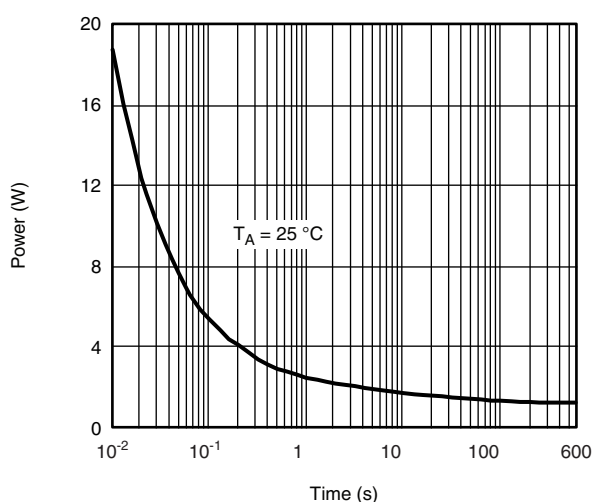
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)


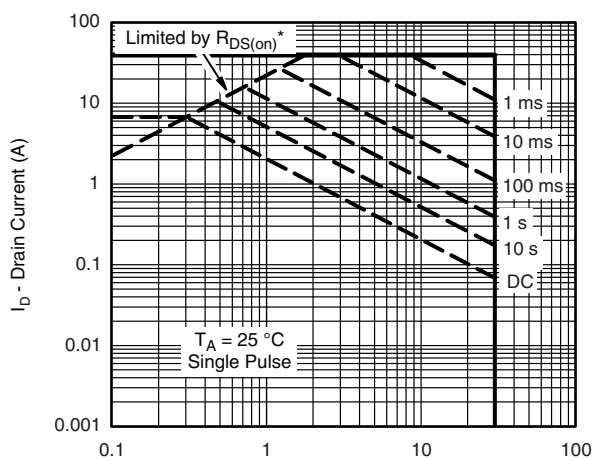
Source-Drain Diode Forward Voltage

 $R_{DS(on)}$ vs. V_{GS} vs. Temperature

Threshold Voltage

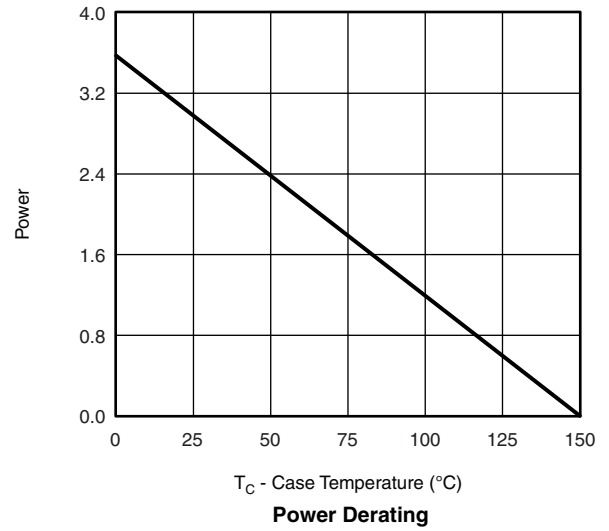
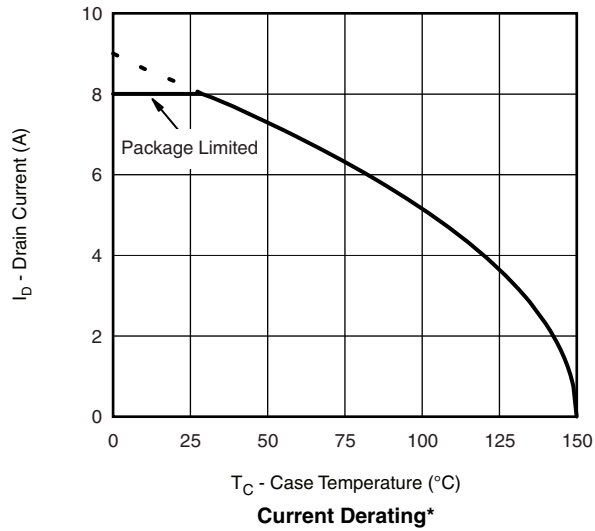


Single Pulse Power

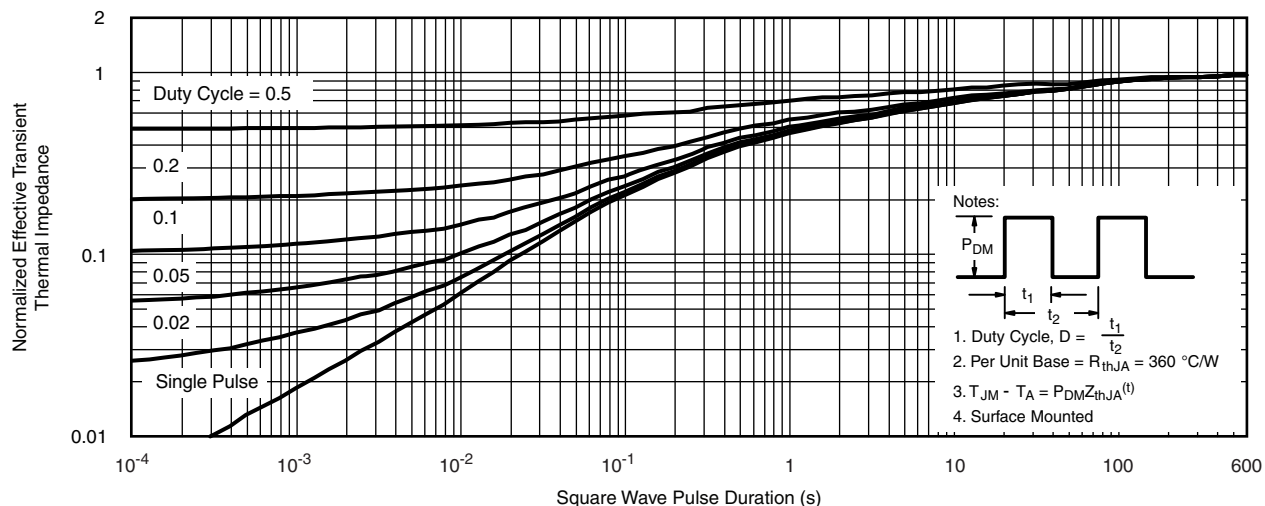
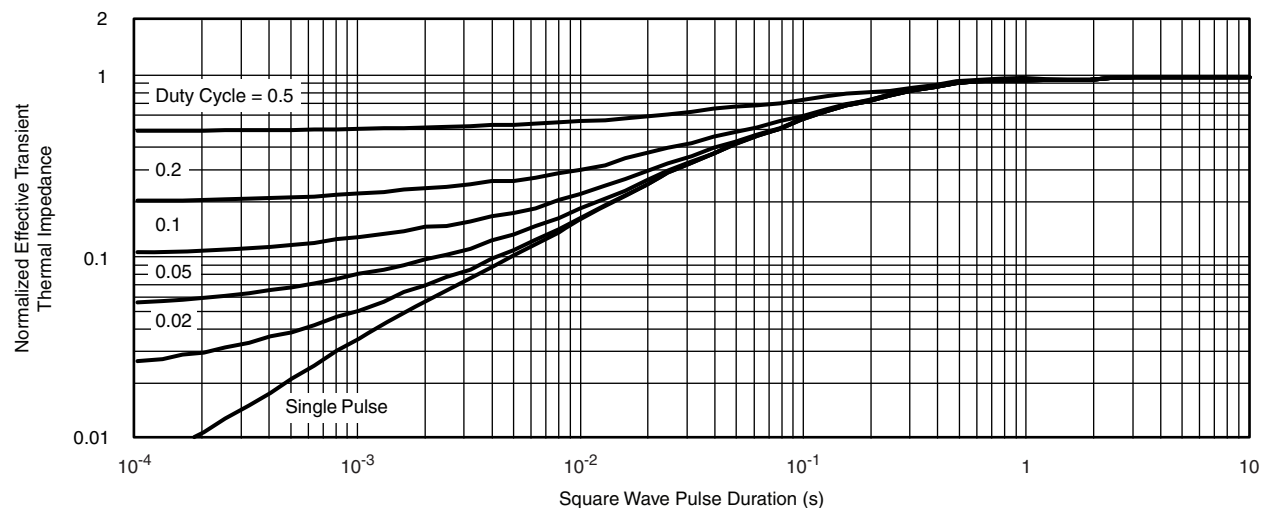


V_{DS} - Drain-to-Source Voltage (V)
 * $V_{DS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



* The power dissipation P_D is based on $T_{J(max)} = 150\text{ }^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?74623.

TSOP: 5/6-LEAD

JEDEC Part Number: MO-193C



5-LEAD TSOP



6-LEAD TSOP



	MILLIMETERS			INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A ₁	0.01	-	0.10	0.0004	-	0.004
A ₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e ₁	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L ₁	0.60 Ref			0.024 Ref		
L ₂	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ ₁	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06						
DWG: 5540						

Recommended Land Pattern For TSOP-5L / TSOP-6L



TSOP 5L



TSOP 6L


Note

- All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022
DWG: 3010



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